



SIGANTIC® RF
...it's watts in the package



Corporate Fact Sheet

FAST FACTS

Founded: 1999
 Employees: 50
 Headquarters: Raleigh, NC
 Patents Awarded: 18
 Patents Pending: 19

MANAGEMENT TEAM

Charles Shalvoy
President & CEO
 Kevin Linthicum
CoFounder & CTO
 Christopher Rauh
VP of Sales & Marketing
 Bruce Cochran
VP of Operations
 Jim DeVivo
Director of Finance

INVESTORS

Alloy Ventures
 ARCH Venture Partners
 Intersouth Partners
 Diamondhead Ventures
 VantagePoint Venture Partners
 Contender Capital

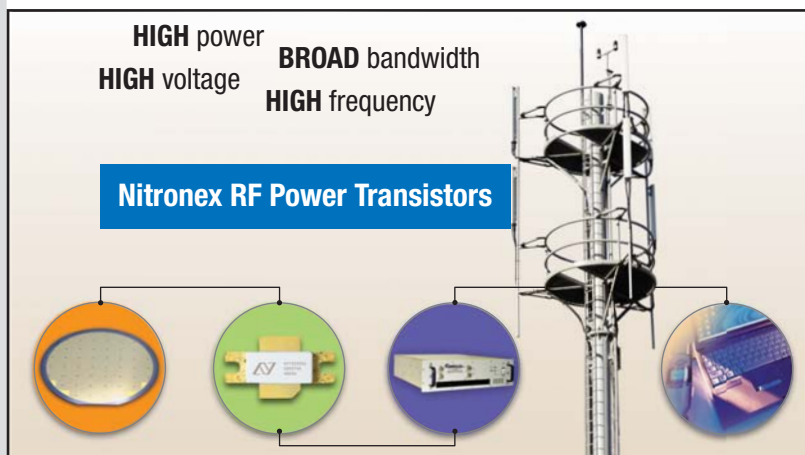
CONTACT INFORMATION

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COMPANY PROFILE

Nitronex is a developer and manufacturer of high performance RF power transistors for the wireless infrastructure market using its patented GaN on silicon process. The company's ability to combine the disciplines of epitaxial growth, wafer processing, device design and wireless application knowledge is unique to the industry. Nitronex's initial products are aimed at next generation RF amplifiers for the WiMAX and 3G markets where it can deliver frequency bandwidth, voltage and power levels not obtainable from current technologies. In addition to wireless infrastructure, Nitronex's patented SIGANTIC® process of growing GaN on silicon can be leveraged in a wide range of markets. Business models exist for die and GaN Epi wafer sales to support developers in markets outside its core focus area.



CORE COMPETENCIES

Epi Growth
 Patented Core Platform Technology – SIGANTIC®

Fabrication
 Established GaN Baseline

Device Design
 Exceptional FET Performance

Intellectual Property
 Dominant Patent Portfolio

WHAT IS UNIQUE ABOUT NITRONEX TECHNOLOGY?

GaN FET (field effect transistor) technology is an ideal choice for next generation power amplifiers serving the 3G and WiMAX markets due to its unique ability to deliver high frequency, high voltage and high power attributes simultaneously. The SIGANTIC platform technology combines the high performance of GaN with the low cost, large area availability of Silicon. Growing GaN on industry standard silicon (vs. sapphire or silicon carbide) provides the economic benefit of large area wafer scaling and lower substrate costs. Silicon substrates also enable the use of standard packaging, test and assembly equipment, resulting in quicker qualifications and additional cost reductions. The significant technical and economic benefits of Nitronex's SIGANTIC process are what will ultimately allow for widespread adoption of GaN based RF devices.

KEY CORPORATE MILESTONES:

- 2006 Industry leading GaN on Silicon process production qualified
- 2006 First GaN RF products in plastic overmold package
- 2005 Approximately 450 prototype devices and over 1000 die have been sampled to over 90 customers worldwide
- 2005 Shipped first 3.5GHz 10W and 50W WiMAX power transistor samples
- 2004 Demonstrated GaN on Silicon MMIC feasibility
- 2004 First commercial revenues
- 2004 Established SIGANTIC products and services business
- 2003 Shipped first WCDMA power transistor samples
- 2002 Established 100mm baseline manufacturing
- 2000 Demonstrated first 100mm GaN on Silicon HEMT
- 2000 Demonstrated first 100mm high quality GaN on Silicon
- 1999 100mm prototype MOCVD reactor commissioned
- 1999 Nitronex Founded

